

The listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1.-27. (Canceled)

28. (Currently Amended) A semiconductor device including at least a pixel portion, a driver circuit for the pixel portion, and a memory portion, ~~characterized in that~~ wherein,

said pixel portion, said driver circuit for the pixel portion, and said memory portion are formed ~~on~~ over the same substrate, and

the semiconductor device has a function for displaying an image in accordance with image data stored in said memory portion.

29. (Currently Amended) A semiconductor device including at least a pixel portion, a driver circuit for the pixel portion, and a memory portion, ~~characterized in that~~ wherein,

said pixel portion is formed ~~on~~ over a first substrate,

said driver circuit for the pixel portion and said memory portion are formed ~~on~~ over a second substrate,

said second substrate is provided in a region except for said pixel portion on said first substrate and is connected with said pixel region such that a signal from said driver circuit for the pixel portion is input to said pixel portion, and

the semiconductor device has a function for displaying an image in accordance with image data stored in said memory portion.

30. (Currently Amended) A semiconductor device according to claim 29, ~~characterized in that~~ wherein said second substrate has the same thickness as said first substrate.

31. (Currently Amended) A semiconductor device according to claim 29 or 30, ~~characterized in that~~ wherein said second substrate is made of the same material as said first substrate.

32. (Currently Amended) A semiconductor device according to claim 29, ~~characterized in that~~ wherein the second substrate is one of a substrate having an insulating surface, an SOI substrate, and a silicon substrate.

33. (Currently Amended) A semiconductor device including at least a pixel portion, a data line side driver circuit, a scanning line side driver circuit, and a memory portion, ~~characterized in that~~ wherein,

said pixel portion is formed ~~on~~ over a first substrate,

said data line side driver circuit and said memory portion are formed ~~on~~ over a second substrate,

said scanning line side driver circuit is integrally formed ~~on~~ over a third substrate,

said second substrate and said third substrate are provided in a region except for said pixel portion ~~on~~ over said first substrate and are connected with said pixel portion such that a signal from said data line side driver circuit and a signal from said scanning line side driver circuit are input to the pixel region, and

the semiconductor device has a function for displaying an image in accordance with image data stored in said memory portion.

34. (Currently Amended) A semiconductor device according to claim 33, ~~characterized in that~~ wherein said second substrate and said third substrate have the same thickness as said first substrate.

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35. (Currently Amended) A semiconductor device according to claim 33 or 34, ~~characterized in that~~ wherein said second substrate and said third substrate are made of the same material as said first substrate.

36. (Currently Amended) A semiconductor device according to claim 33, ~~characterized in that~~ wherein said second substrate and said third substrate are one of a substrate having an insulating surface, an SOI substrate, and a silicon substrate.

37. (Currently Amended) A semiconductor device according to any one of claims 28-30, 32-34, or 36, ~~characterized in that~~ wherein said semiconductor device has a function of displaying a still image in accordance with the image data stored in said memory portion.

38. (Currently Amended) A semiconductor device according to any one of claims 28-30, 32-34, or 36, ~~characterized in that~~ wherein said semiconductor device includes a memory control circuit, and

said memory control circuit and said memory portion are formed ~~on~~ over the same substrate.

39. (Currently Amended) A semiconductor device according to any one of claims 28-30, 32-34, or 36, ~~characterized in that~~ wherein said semiconductor device is composed of a first region having a function of displaying the image and a second region having a function of supplying the image data to said first region,

said first region includes the substrate on which the pixel portion is formed, and

the semiconductor device includes a first display method of displaying the image in accordance with the image data supplied from said second region and a second

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display method of displaying the image in accordance with the image data stored in the memory portion provided in said first region.

40. (Currently Amended) A semiconductor device of claim 39, ~~characterized in that~~ wherein power consumed in said semiconductor device by said second display method is 70 % or lower of power consumed in said semiconductor device by said first display method.

41. (Currently Amended) A semiconductor device of claim 39, ~~characterized in that~~ wherein when said second display method is performed, 50 % or higher of power consumed in said semiconductor device is consumed in said first region.

42. (Currently Amended) A semiconductor device of claim 39, ~~characterized in that~~ wherein when said second display method is performed, 90 % or higher of power consumed in said semiconductor device is consumed in said first region.

43. (Currently Amended) A semiconductor device of claim 39, ~~characterized in that~~ wherein said first display method is controlled by a CPU provided in said second region,

said second display method is controlled by a control circuit provided in said first region, and

said second display method can be performed with a state in which a power source of said CPU is turned off.

44. (Currently Amended) A semiconductor device group composed of a first semiconductor device having a function of displaying an image and a second semiconductor device having a function of supplying image data to said first semiconductor device,

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said first semiconductor device is a semiconductor device according to any one of claims 28-30, 32-34, or 36, ~~characterized in that~~ wherein,

said semiconductor device group includes a first display method of displaying the image data supplied from said second semiconductor device and a second display method of displaying the image in accordance with the image data stored in the memory portion included in said first semiconductor device.

45. (Currently Amended) A semiconductor device group of claim 44, ~~characterized in that~~ wherein power consumed in the entire said semiconductor device group by said second display method is 70 % or lower of power consumed in said entire semiconductor device group by said first display method.

46. (Currently Amended) A semiconductor device group of claim 44, ~~characterized in that~~ wherein when said second display method is performed, 50 % or higher of power consumed in said entire semiconductor device group is consumed in said first semiconductor device.

47. (Currently Amended) A semiconductor device group of claim 44, ~~characterized in that~~ wherein when said second display method is performed, 90 % or higher of power consumed in said entire semiconductor device group is consumed in said first semiconductor device.

48. (Currently Amended) A semiconductor device group of claim 44, ~~characterized in that~~ wherein said second display method can be performed by only said first semiconductor device.

49. (Currently Amended) A semiconductor device of any one of claims 28-30, 32-34, or 36, ~~characterized in that~~ wherein said memory portion has a memory capacity of 100 kbit to 10 Gbit.

50. (Currently Amended) A semiconductor device according to any one of claims 28-30, 32-34, or 36, ~~characterized in that~~ wherein said memory portion has a memory capacity of 1 Mbit to 128 Mbit.

51. (Currently Amended) A semiconductor device according to any one of claims 28-30, 32-34, or 36, ~~characterized in that~~ wherein said memory portion is composed of one of an SRAM, a DRAM, and an EEPROM.

52. (Currently Amended) A semiconductor device according to any one of claims 28-30, 32-34, or 36, ~~characterized in that~~ wherein said memory portion is composed of a combination of an SRAM, a DRAM, and an EEPROM.

*Amended*  
53. (Currently Amended) A semiconductor device according to any one of claims 28-30, 32-34, or 36, ~~characterized in that~~ wherein said semiconductor device is one of an active matrix liquid crystal display device, a passive matrix liquid crystal display device, an active matrix EL display device, and a passive matrix EL display device.

54. (Currently Amended) A semiconductor device according to any one of claims 28-30, 32-34, or 36, ~~characterized in that~~ wherein said semiconductor device is one selected from a display, a video camera, a head mounted display, a DVD player, a goggle type display, a personal computer, a cellular phone, and a car audio system.